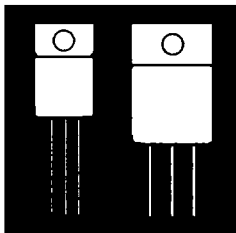


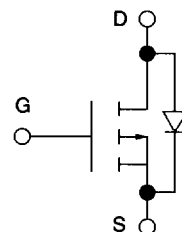
# POWER MOSFET IN HERMETIC ISOLATED JEDEC PACKAGE, P-CHANNEL



60V To 500V P-Channel MOSFET In A Hermetic Package

## FEATURES

- Isolated Hermetic Metal Package
- P-Channel
- Fast Switching, Low Drive Current
- Ease of Paralleling For Added Power
- Available Screened To MIL-S-19500, TX, TXV And S Level
- Ceramic Feedthroughs Available



## DESCRIPTION

This series of hermetically packaged products feature the latest advanced MOSFET and packaging technology. They are ideally suited for Military requirements where small size, high performance and high reliability are required, and in applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers and high energy pulse circuits.

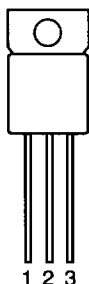
## MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted.)

BASIC PART NUMBER	V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)		I <sub>D</sub> (A)
		TO-257AA	TO-254AA	
OM23P06	60	.16	.12	23
OM20P10	100	.20	.16	20
OM12P10	100	.34	.30	12
OM8P20	200	.80	.75	8
OM8P25	250	2.08	2.00	8
OM2P50	500	6.10	6.00	2

3.1

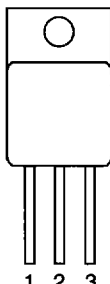
## PIN CONNECTION

### TO-257AA



Pin 1: Drain  
 Pin 2: Source  
 Pin 3: Gate

### TO-254AA



## ORDERING INFORMATION

Example:  
 OM20P10 ST M  
 Basic Part Case Screening  
 Number Style Level

Case Style:  
 ST = TO-257AA  
 SA = TO-254AA

Standard Products are supplied with glass feedthroughs. For ceramic feedthroughs, add letter "C" to part number: Example - OM20P10CST.

**ELECTRICAL CHARACTERISTICS: (T<sub>c</sub> = 25°C unless otherwise noted)**  
**STATIC P/N OM23P06ST/OM23P06SA (60V)**

Parameter	Min.	Max.	Units	Test Conditions
BV <sub>DS</sub> Drain-Source Breakdown Voltage	60		V	V <sub>GS</sub> = 0, I <sub>b</sub> = 250 μA
V <sub>GS(th)</sub> Gate-Threshold Voltage	2	4.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>b</sub> = 1.0 mA
I <sub>SS</sub> Gate-Body Leakage		± 100	nA	V <sub>GS</sub> = ± 20 V
I <sub>DSS</sub> Zero Gate Voltage Drain Current		0.1	mA	V <sub>DS</sub> = Max. Rat., V <sub>GS</sub> = 0
		1.0	mA	T <sub>c</sub> = 125°C
V <sub>DS(on)</sub> Static Drain-Source On-State Voltage <sup>1</sup>		3.5	V	V <sub>GS</sub> = 10 V, I <sub>b</sub> = 23 A
R <sub>DS(on)</sub> Static Drain-Source On-State Resistance <sup>1</sup>		.16	Ω	V <sub>GS</sub> = 10 V, I <sub>b</sub> = 11.5 A
R <sub>DS(on)</sub> Static Drain-Source On-State Resistance <sup>1</sup>		.32	Ω	V <sub>GS</sub> = 10 V, I <sub>b</sub> = 11.5 A, T <sub>c</sub> = 125°C

**DYNAMIC**

Parameter	Min.	Max.	Units	Test Conditions
g <sub>m</sub> Forward Transconductance <sup>1</sup>		5.0	S (Ω)	V <sub>DS</sub> ≥ 2 V <sub>DS(on)</sub> , I <sub>b</sub> = 11.5 A
C <sub>iss</sub> Input Capacitance		1700	pF	V <sub>GS</sub> = 0
C <sub>oss</sub> Output Capacitance		900	pF	V <sub>DS</sub> = 25 V
C <sub>res</sub> Reverse Transfer Capacitance		400	pF	f = 1 MHz
t <sub>don</sub> Turn-On Delay Time		30	ns	
t <sub>r</sub> Rise Time		170	ns	V <sub>DS</sub> = 25 V, I <sub>b</sub> = 23 A
t <sub>deon</sub> Turn-Off Delay Time		140	ns	R <sub>θ</sub> = 13 Ω
t <sub>f</sub> Fall Time		120	ns	

**BODY-DRAIN DIODE RATINGS AND CHARACTERISTICS**

Parameter	Min.	Max.	Units	Test Conditions
I <sub>S</sub> Continuous Source Current (Body Diode)		23	A	Modified MOSPOWER symbol showing the integral P-N Junction rectifier.
I <sub>SM</sub> Source Current <sup>1</sup> (Body Diode)		75	A	
V <sub>SD</sub> Diode Forward Voltage <sup>1</sup>		3.5	V	I <sub>S</sub> = 23 A, V <sub>GS</sub> = 0
t <sub>r</sub> Reverse Recovery Time		200	ns	I <sub>F</sub> = 23 A, dI <sub>F</sub> /dS = 100 A/μs

<sup>1</sup> Pulse Test: Pulse Width ≤ 300μsec, Duty Cycle ≤ 2%.

**ELECTRICAL CHARACTERISTICS: (T<sub>c</sub> = 25°C unless otherwise noted)**  
**STATIC P/N OM20P10ST/OM20P10SA (100V)**

Parameter	Min.	Max.	Units	Test Conditions
BV <sub>DS</sub> Drain-Source Breakdown Voltage	100		V	V <sub>GS</sub> = 0, I <sub>b</sub> = 250 μA
V <sub>GS(th)</sub> Gate-Threshold Voltage	2	4.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>b</sub> = 1.0 mA
I <sub>SS</sub> Gate-Body Leakage		± 100	nA	V <sub>GS</sub> = ± 20 V
I <sub>DSS</sub> Zero Gate Voltage Drain Current		.01	mA	V <sub>DS</sub> = Max. Rat., V <sub>GS</sub> = 0
		.10	mA	T <sub>c</sub> = 125°C
V <sub>DS(on)</sub> Static Drain-Source On-State Voltage <sup>1</sup>		4.2	V	V <sub>GS</sub> = 10 V, I <sub>b</sub> = 20 A
R <sub>DS(on)</sub> Static Drain-Source On-State Resistance <sup>1</sup>		.20	Ω	V <sub>GS</sub> = 10 V, I <sub>b</sub> = 10 A
R <sub>DS(on)</sub> Static Drain-Source On-State Resistance <sup>1</sup>		.40	Ω	V <sub>GS</sub> = 10 V, I <sub>b</sub> = 10 A, T <sub>c</sub> = 125°C

**DYNAMIC**

Parameter	Min.	Max.	Units	Test Conditions
g <sub>m</sub> Forward Transconductance <sup>1</sup>		5.0	S (Ω)	V <sub>DS</sub> ≥ 2 V <sub>DS(on)</sub> , I <sub>b</sub> = 10 A
C <sub>iss</sub> Input Capacitance		2000	pF	V <sub>GS</sub> = 0
C <sub>oss</sub> Output Capacitance		950	pF	V <sub>DS</sub> = 25 V
C <sub>res</sub> Reverse Transfer Capacitance		400	pF	f = 1 MHz
t <sub>don</sub> Turn-On Delay Time		45	ns	
t <sub>r</sub> Rise Time		200	ns	V <sub>DS</sub> = 25 V, I <sub>b</sub> = 10 A
t <sub>deon</sub> Turn-Off Delay Time		150	ns	R <sub>θ</sub> = 50 Ω
t <sub>f</sub> Fall Time		150	ns	

**BODY-DRAIN DIODE RATINGS AND CHARACTERISTICS**

Parameter	Min.	Max.	Units	Test Conditions
I <sub>S</sub> Continuous Source Current (Body Diode)		20	A	Modified MOSPOWER symbol showing the integral P-N Junction rectifier.
I <sub>SM</sub> Source Current <sup>1</sup> (Body Diode)		80	A	
V <sub>SD</sub> Diode Forward Voltage <sup>1</sup>		4.0	V	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0
t <sub>r</sub> Reverse Recovery Time		475	ns	I <sub>F</sub> = 20 A, dI <sub>F</sub> /dS = 100 A/μs

<sup>1</sup> Pulse Test: Pulse Width ≤ 300μsec, Duty Cycle ≤ 2%.

**ELECTRICAL CHARACTERISTICS: (T<sub>C</sub> = 25°C unless otherwise noted)  
STATIC P/N OM12P10ST/OM12P10SA (100V)**

Parameter	Min.	Max.	Units	Test Conditions
BV <sub>DSS</sub> Drain-Source Breakdown Voltage	100		V	V <sub>GS</sub> = 0, I <sub>B</sub> = 250 μA
V <sub>GS(th)</sub> Gate-Threshold Voltage	2	4.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>B</sub> = 1.0 mA
I <sub>DSS</sub> Gate-Body Leakage		± 100	nA	V <sub>GS</sub> = ± 20 V
I <sub>DSS</sub> Zero Gate Voltage Drain Current		.01	mA	V <sub>GS</sub> = Max. Rat., V <sub>DS</sub> = 0
		.10	mA	V <sub>GS</sub> = Max. Rat., V <sub>DS</sub> = 0, T <sub>C</sub> = 125°C
V <sub>DS(on)</sub> Static Drain-Source On-State Voltage <sup>1</sup>		4.2	V	V <sub>GS</sub> = 10 V, I <sub>B</sub> = 12 A
R <sub>DS(on)</sub> Static Drain-Source On-State Resistance <sup>1</sup>		.34	Ω	V <sub>GS</sub> = 10 V, I <sub>B</sub> = 6 A
R <sub>DS(on)</sub> Static Drain-Source On-State Resistance <sup>1</sup>		.68	Ω	V <sub>GS</sub> = 10 V, I <sub>B</sub> = 6 A, T <sub>C</sub> = 125°C
		.60	Ω	

**DYNAMIC**

Symbol	Min.	Max.	Units	Test Conditions
S <sub>th</sub> Forward Transconductance <sup>1</sup>	2.0		S (Ω)	V <sub>GS</sub> ≥ 2 V <sub>DS(on)</sub> , I <sub>B</sub> = 6 A
C <sub>iss</sub> Input Capacitance		920	pF	V <sub>GS</sub> = 0
C <sub>oss</sub> Output Capacitance		575	pF	V <sub>GS</sub> = 25 V
C <sub>res</sub> Reverse Transfer Capacitance		200	pF	f = 1 MHz
t <sub>don</sub> Turn-On Delay Time		50	ns	V <sub>GS</sub> = 25 V, I <sub>B</sub> = 6 A
t <sub>r</sub> Rise Time		150	ns	R <sub>θ</sub> = 50 Ω
t <sub>deon</sub> Turn-Off Delay Time		150	ns	
t <sub>f</sub> Fall Time		150	ns	

**BODY-DRAIN DIODE RATINGS AND CHARACTERISTICS**

Symbol	Min.	Max.	Units	Test Conditions
I <sub>S</sub> Continuous Source Current (Body Diode)		12	A	
I <sub>SM</sub> Source Current <sup>1</sup> (Body Diode)		28	A	
V <sub>SD</sub> Diode Forward Voltage <sup>1</sup>		5.5	V	I <sub>F</sub> = 12 A, V <sub>GS</sub> = 0
t <sub>r</sub> Reverse Recovery Time		450	ns	I <sub>F</sub> = 12 A, dI <sub>F</sub> /dS = 100 A/μs

<sup>1</sup> Pulse Test: Pulse Width ≤ 300μsec, Duty Cycle ≤ 2%.

**ELECTRICAL CHARACTERISTICS: (T<sub>C</sub> = 25°C unless otherwise noted)  
STATIC P/N OM8P20ST/OM8P20SA (200V)**

Parameter	Min.	Max.	Units	Test Conditions
BV <sub>DSS</sub> Drain-Source Breakdown Voltage	200		V	V <sub>GS</sub> = 0, I <sub>B</sub> = 250 μA
V <sub>GS(th)</sub> Gate-Threshold Voltage	2	4.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>B</sub> = 1.0 mA
I <sub>DSS</sub> Gate-Body Leakage		± 100	nA	V <sub>GS</sub> = ± 20 V
I <sub>DSS</sub> Zero Gate Voltage Drain Current		.2	mA	V <sub>GS</sub> = Max. Rat., V <sub>DS</sub> = 0
		1.0	mA	V <sub>GS</sub> = Max. Rat., V <sub>DS</sub> = 0, T <sub>C</sub> = 125°C
V <sub>DS(on)</sub> Static Drain-Source On-State Voltage <sup>1</sup>		7.0	V	V <sub>GS</sub> = 10 V, I <sub>B</sub> = 8 A
R <sub>DS(on)</sub> Static Drain-Source On-State Resistance <sup>1</sup>		.80	Ω	V <sub>GS</sub> = 10 V, I <sub>B</sub> = 4 A
R <sub>DS(on)</sub> Static Drain-Source On-State Resistance <sup>1</sup>		.75	Ω	
R <sub>DS(on)</sub> Static Drain-Source On-State Resistance <sup>1</sup>		1.60	Ω	V <sub>GS</sub> = 10 V, I <sub>B</sub> = 4 A, T <sub>C</sub> = 125°C
		1.50	Ω	

**DYNAMIC**

Symbol	Min.	Max.	Units	Test Conditions
S <sub>th</sub> Forward Transconductance <sup>1</sup>	2.0		S (Ω)	V <sub>GS</sub> ≥ 2 V <sub>DS(on)</sub> , I <sub>B</sub> = 4 A
C <sub>iss</sub> Input Capacitance		1600	pF	V <sub>GS</sub> = 0
C <sub>oss</sub> Output Capacitance		400	pF	V <sub>GS</sub> = 25 V
C <sub>res</sub> Reverse Transfer Capacitance		120	pF	f = 1 MHz
t <sub>don</sub> Turn-On Delay Time		40	ns	V <sub>GS</sub> = 10 V, I <sub>B</sub> = 4 A
t <sub>r</sub> Rise Time		120	ns	R <sub>θ</sub> = 50 Ω
t <sub>deon</sub> Turn-Off Delay Time		100	ns	
t <sub>f</sub> Fall Time		80	ns	

**BODY-DRAIN DIODE RATINGS AND CHARACTERISTICS**

Symbol	Min.	Max.	Units	Test Conditions
I <sub>S</sub> Continuous Source Current (Body Diode)		8	A	
I <sub>SM</sub> Source Current <sup>1</sup> (Body Diode)		30	A	
V <sub>SD</sub> Diode Forward Voltage <sup>1</sup>		3.0	V	I <sub>F</sub> = 8 A, V <sub>GS</sub> = 0
t <sub>r</sub> Reverse Recovery Time		475	ns	I <sub>F</sub> = 8 A, dI <sub>F</sub> /dS = 100 A/μs

<sup>1</sup> Pulse Test: Pulse Width ≤ 300μsec, Duty Cycle ≤ 2%.

**ELECTRICAL CHARACTERISTICS: (T<sub>C</sub> = 25°C unless otherwise noted)**  
**STATIC P/N OM8P25ST/OM8P25SA (250V)**

Parameter	Min.	Max.	Units	Test Conditions
BV <sub>DSS</sub> Drain-Source Breakdown Voltage	250		V	V <sub>GS</sub> = 0, I <sub>B</sub> = 250 μA
V <sub>GS(th)</sub> Gate-Threshold Voltage	2	4.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>B</sub> = 250 μA
I <sub>loss</sub> Gate-Body Leakage		± 100	nA	V <sub>GS</sub> = ± 20 V
I <sub>DSS</sub> Zero Gate Voltage Drain Current		.20	mA	V <sub>GS</sub> = Max. Rel., V <sub>DS</sub> = 0
		1.0	mA	V <sub>GS</sub> = 0.8 Max. Rat., V <sub>DS</sub> = 0, T <sub>C</sub> = 125°C
V <sub>DS(on)</sub> Static Drain-Source On-State Voltage <sup>1</sup>		18	V	V <sub>GS</sub> = 10 V, I <sub>B</sub> = 8 A
R <sub>DS(on)</sub> Static Drain-Source On-State Resistance <sup>1</sup>		2.08	Ω	V <sub>GS</sub> = 10 V, I <sub>B</sub> = 4 A
R <sub>DS(on)</sub> Static Drain-Source On-State Resistance <sup>1</sup>		2.00	Ω	V <sub>GS</sub> = 10 V, I <sub>B</sub> = 4 A, T <sub>C</sub> = 125°C
R <sub>DS(on)</sub> Static Drain-Source On-State Resistance <sup>1</sup>		4.16	Ω	V <sub>GS</sub> = 10 V, I <sub>B</sub> = 4 A, T <sub>C</sub> = 125°C

**DYNAMIC**

g <sub>m</sub> Forward Transconductance <sup>1</sup>	3.0		S (Ω)	V <sub>GS</sub> ≥ 2 V <sub>DS(on)</sub> , I <sub>B</sub> = 4 A
C <sub>iss</sub> Input Capacitance		2200	pF	V <sub>GS</sub> = 0
C <sub>oss</sub> Output Capacitance		500	pF	V <sub>GS</sub> = 25 V
C <sub>res</sub> Reverse Transfer Capacitance		300	pF	f = 1 MHz
t <sub>don</sub> Turn-On Delay Time		40	ns	V <sub>GS</sub> = 25 V, I <sub>B</sub> = 4 A
t <sub>r</sub> Rise Time		100	ns	F <sub>0</sub> = 50 Ω
t <sub>off</sub> Turn-Off Delay Time		160	ns	
t <sub>f</sub> Fall Time		90	ns	

**BODY-DRAIN DIODE RATINGS AND CHARACTERISTICS**

I <sub>S</sub> Continuous Source Current (Body Diode)		8	A	Modified MOSPOWER symbol showing the integral P-N Junction rectifier.
I <sub>SM</sub> Source Current <sup>1</sup> (Body Diode)		24	A	
V <sub>SD</sub> Diode Forward Voltage <sup>1</sup>		5	V	I <sub>F</sub> = 8 A, V <sub>GS</sub> = 0
t <sub>r</sub> Reverse Recovery Time		400	ns	I <sub>F</sub> = 8 A, dI <sub>F</sub> /ds = 100 A/μs

<sup>1</sup> Pulse Test: Pulse Width ≤ 300μsec, Duty Cycle ≤ 2%.

**ELECTRICAL CHARACTERISTICS: (T<sub>C</sub> = 25°C unless otherwise noted)**  
**STATIC P/N OM2P50ST/OM2P50SA (500V)**

Parameter	Min.	Max.	Units	Test Conditions
BV <sub>DSS</sub> Drain-Source Breakdown Voltage	500		V	V <sub>GS</sub> = 0, I <sub>B</sub> = 5.0 mA
V <sub>GS(th)</sub> Gate-Threshold Voltage	2	4.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>B</sub> = 1.0 mA
I <sub>loss</sub> Gate-Body Leakage		± 100	nA	V <sub>GS</sub> = ± 20 V
I <sub>DSS</sub> Zero Gate Voltage Drain Current		.25	mA	V <sub>GS</sub> = 425 V, V <sub>DS</sub> = 0
		2.5	mA	T <sub>C</sub> = 100° C
V <sub>DS(on)</sub> Static Drain-Source On-State Voltage <sup>1</sup>		6.1	V	V <sub>GS</sub> = 10 V, I <sub>B</sub> = 1.0 A
R <sub>DS(on)</sub> Static Drain-Source On-State Resistance <sup>1</sup>		6.1	Ω	V <sub>GS</sub> = 10 V, I <sub>B</sub> = 1.0 A
R <sub>DS(on)</sub> Static Drain-Source On-State Resistance <sup>1</sup>		6.0	Ω	V <sub>GS</sub> = 10 V, I <sub>B</sub> = 1.0 A, T <sub>C</sub> = 125°C
R <sub>DS(on)</sub> Static Drain-Source On-State Resistance <sup>1</sup>		12.2	Ω	V <sub>GS</sub> = 10 V, I <sub>B</sub> = 1.0 A, T <sub>C</sub> = 125°C

**DYNAMIC**

g <sub>m</sub> Forward Transconductance <sup>1</sup>	.5		S(Ω)	V <sub>GS</sub> ≥ 2 V <sub>DS(on)</sub> , I <sub>B</sub> = 1.0 A
C <sub>iss</sub> Input Capacitance		100	pF	V <sub>GS</sub> = 0
C <sub>oss</sub> Output Capacitance		200	pF	V <sub>GS</sub> = 25 V
C <sub>res</sub> Reverse Transfer Capacitance		80	pF	f = 1 MHz
t <sub>don</sub> Turn-On Delay Time		50	ns	V <sub>GS</sub> = 125 V, I <sub>B</sub> = 1.0 A
t <sub>r</sub> Rise Time		100	ns	F <sub>0</sub> = 50 Ω
t <sub>off</sub> Turn-Off Delay Time		150	ns	
t <sub>f</sub> Fall Time		50	ns	

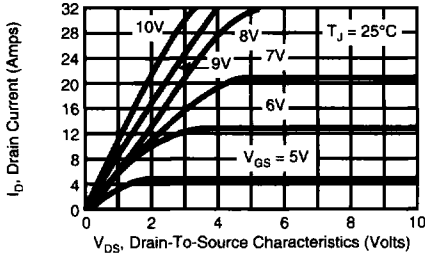
**BODY-DRAIN DIODE RATINGS AND CHARACTERISTICS**

I <sub>S</sub> Continuous Source Current (Body Diode)		2.0	A	Modified MOSPOWER symbol showing the integral P-N Junction rectifier.
I <sub>SM</sub> Source Current <sup>1</sup> (Body Diode)		8.0	A	
V <sub>SD</sub> Diode Forward Voltage <sup>1</sup>		1.8	V	I <sub>F</sub> = 2.0 A, V <sub>GS</sub> = 0
t <sub>r</sub> Reverse Recovery Time		125	ns	I <sub>F</sub> = 2.0 A, dI <sub>F</sub> /ds = 100 A/μs

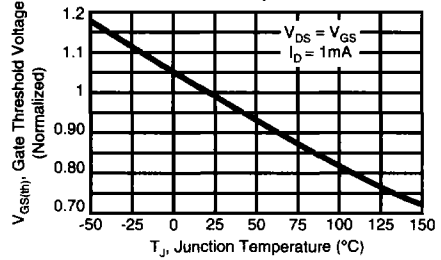
<sup>1</sup> Pulse Test: Pulse Width ≤ 300μsec, Duty Cycle ≤ 2%.

# TYPICAL ELECTRICAL CHARACTERISTICS, OM23P06

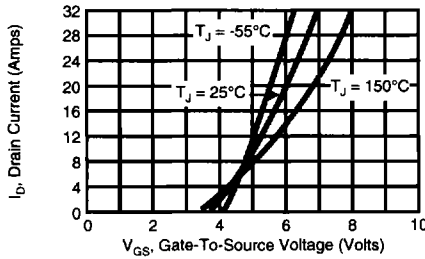
**On-Region Characteristics**



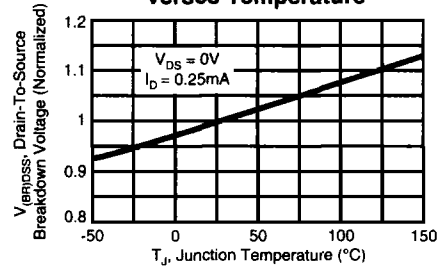
**Gate-Threshold Variation With Temperature**



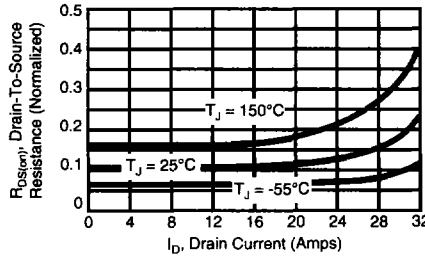
**Transfer Characteristics**



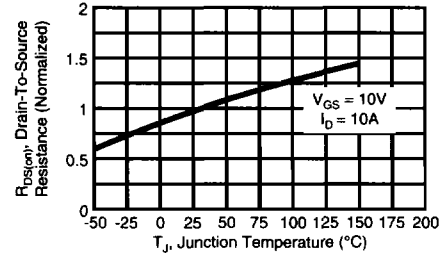
**Normalized Breakdown Voltage versus Temperature**



**On-Resistance versus Drain Current**

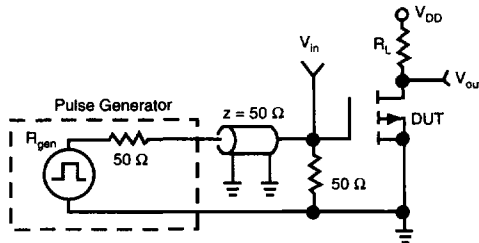


**Normalized On-Resistance versus Temperature**

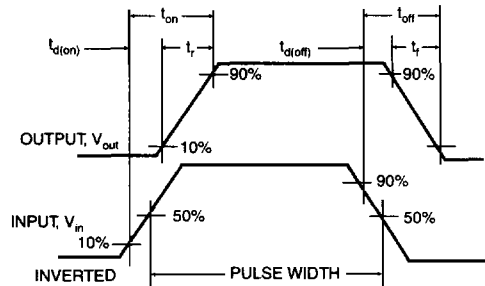


3.1

## SWITCHING TEST CIRCUIT



## SWITCHING WAVEFORMS



**ABSOLUTE MAXIMUM RATINGS** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

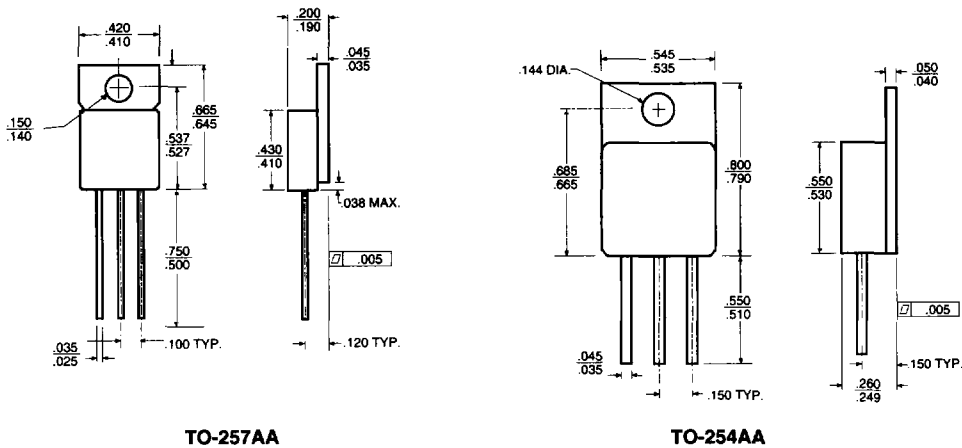
Parameter	OM23P06	OM20P10	OM12P10	OM8P20	OM8P25	OM2P50	Units
$V_{DS}$ Drain-Source Voltage	60	100	100	200	250	500	V
$V_{DGR}$ Drain-Gate Voltage ( $R_{GS} = 1\text{ M}\Omega$ )	60	100	100	200	250	500	V
$I_D$ Continuous Drain Current <sup>2</sup>	23	20	12	8	8	2	A
$I_{DM}$ Pulsed Drain Current <sup>1,2</sup>	75	80	28	30	24	8	A
$V_{GS}$ Gate-Source Voltage	$\pm 20$	$\pm 20$	$\pm 20$	$\pm 20$	$\pm 20$	$\pm 20$	V
$P_D$ Maximum Power Dissipation	118	110	72	110	72	72	W
$R_{\theta JC}$ Junction-To-Case	1.32	1.1	1.76	1.1	1.76	1.76	$^\circ\text{C/W}$
$T_J$ Operating and							
$T_{stg}$ Storage Temperature Range	-55 to 150	-55 to 150	-55 to 150	-55 to 150	-55 to 150	-55 to 150	$^\circ\text{C}$
Linear Derating Factor	.76	.91	.57	.91	.57	.57	$\text{W}/^\circ\text{C}$
Lead Temperature (1/16" from case for 10 secs.)	300	300	300	300	300	300	$^\circ\text{C}$

1 Pulse Test: Pulse width  $\leq 300\ \mu\text{sec}$ . Duty Cycle  $\leq 2\%$ .  
 2 Package Pin Limitations: TO-257AA, 15 Amps; TO-254AA, 25 Amps.

**PACKAGE LIMITATIONS**

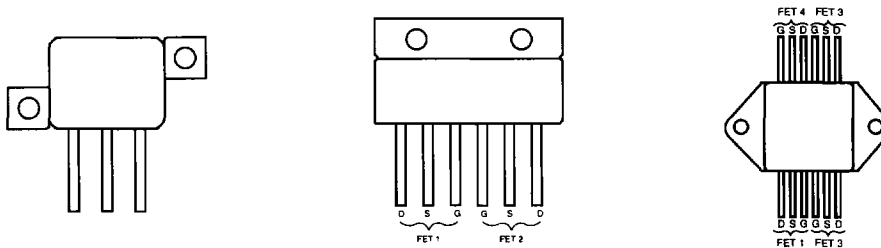
Parameters	TO-257AA	TO-254AA	Unit
$I_D$ Continuous Drain Current	15	25	A
Linear Derating Factor, Junction-to-Ambient	.015	.020	$\text{W}/^\circ\text{C}$
$R_{\theta JA}$ Thermal Resistance, Junction-to-Ambient (Free Air Operation)	67	50	$^\circ\text{C/W}$

**MECHANICAL OUTLINE**



3.1

**PACKAGE OPTIONS**



Note: MOSFETs are also available in Z-Pak, dual and quad pak styles. Please call the factory for more information.